

128K x 8 Static RAM

Features

- Pin and function compatible with CY7C1019BV33
- High speed
 - $t_{AA} = 8, 10, 12, 15$ ns
- CMOS for optimum speed/power
- Data retention at 2.0V
- Center power/ground pinout
- Automatic power-down when deselected
- Easy memory expansion with \overline{CE} and \overline{OE} options
- Available in 32-pin TSOP II and 400-mil SOJ package

Functional Description

The CY7C1019CV33 is a high-performance CMOS static RAM organized as 131,072 words by 8 bits. Easy memory expansion is provided by an active LOW Chip Enable (\overline{CE}), an active LOW Output Enable (\overline{OE}), and three-state drivers. This

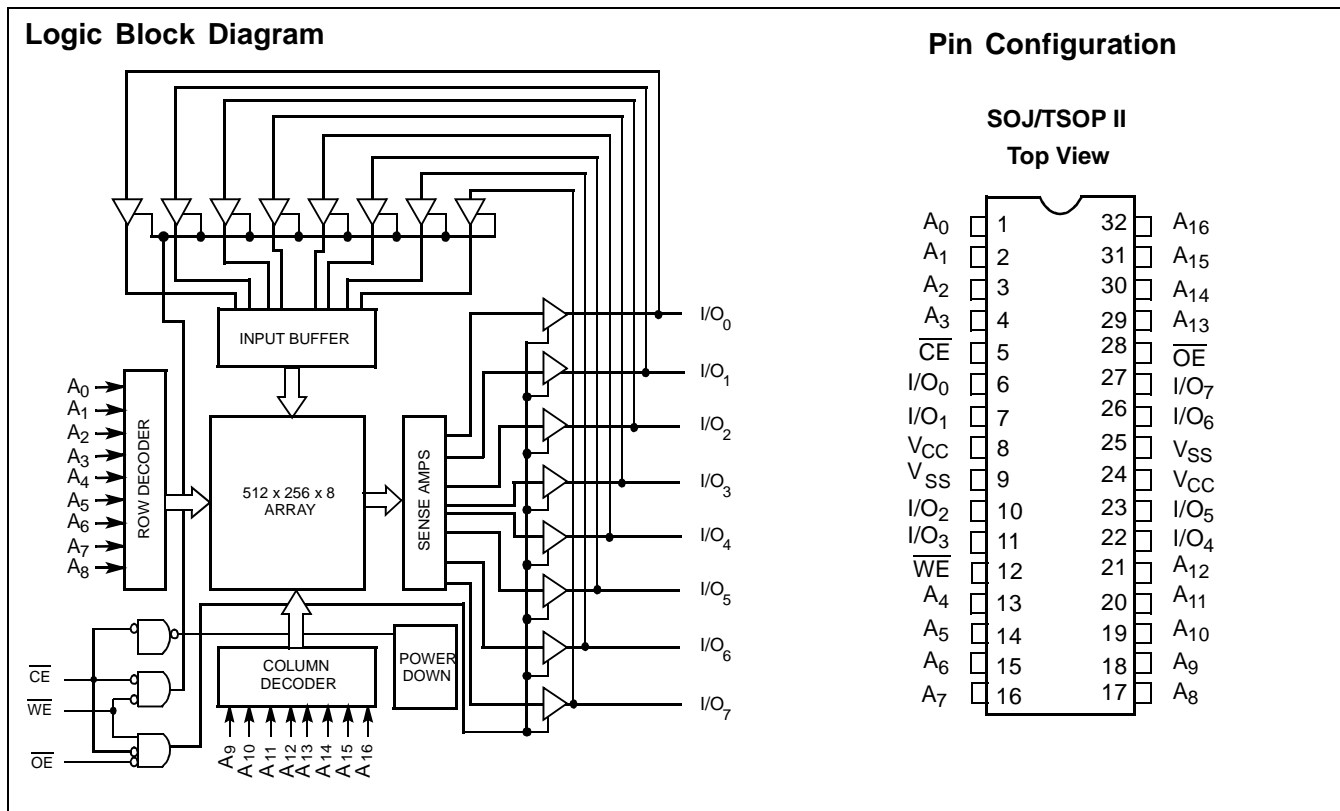
device has an automatic power-down feature that significantly reduces power consumption when deselected.

Writing to the device is accomplished by taking Chip Enable (\overline{CE}) and Write Enable (\overline{WE}) inputs LOW. Data on the eight I/O pins (I/O_0 through I/O_7) is then written into the location specified on the address pins (A_0 through A_{16}).

Reading from the device is accomplished by taking Chip Enable (\overline{CE}) and Output Enable (\overline{OE}) LOW while forcing Write Enable (\overline{WE}) HIGH. Under these conditions, the contents of the memory location specified by the address pins will appear on the I/O pins.

The eight input/output pins (I/O_0 through I/O_7) are placed in a high-impedance state when the device is deselected (\overline{CE} HIGH), the outputs are disabled (\overline{OE} HIGH), or during a write operation (\overline{CE} LOW, and \overline{WE} LOW).

The CY7C1019CV33 is available in a standard 32-pin TSOP II and 400-mil-wide SOJ.



Selection Guide

	7C1019CV33-8	7C1019CV33-10	7C1019CV33-12	7C1019CV33-15	Unit
Maximum Access Time	8	10	12	15	ns
Maximum Operating Current	85	80	75	70	mA
Maximum Standby Current	5	5	5	5	mA

Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature-65°C to +150°C
 Ambient Temperature with Power Applied.....-55°C to +125°C
 Supply Voltage on V_{CC} to Relative GND^[1] ... -0.5V to + 4.6V
 DC Voltage Applied to Outputs in High-Z State^[1]-0.5V to V_{CC} + 0.5V
 DC Input Voltage^[1].....-0.5V to V_{CC} + 0.5V

Current into Outputs (LOW)..... 20 mA
 Static Discharge Voltage..... >2001V (per MIL-STD-883, Method 3015)
 Latch-up Current..... >200 mA

Operating Range

Range	Ambient Temperature	V _{CC}
Commercial	0°C to +70°C	3.3V ± 10%
Industrial	-40°C to +85°C	3.3V ± 10%

Electrical Characteristics Over the Operating Range

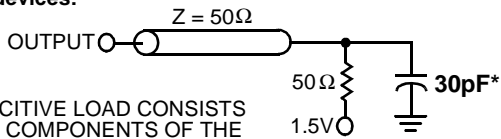
Parameter	Description	Test Conditions	7C1019CV33 -8		7C1019CV33 -10		7C1019CV33 -12		7C1019CV33 -15		Unit
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
V _{OH}	Output HIGH Voltage	V _{CC} = Min., I _{OH} = -4.0 mA	2.4		2.4		2.4		2.4		V
V _{OL}	Output LOW Voltage	V _{CC} = Min., I _{OL} = 8.0 mA		0.4		0.4		0.4		0.4	V
V _{IH}	Input HIGH Voltage		2.0	V _{CC} + 0.3	2.0	V _{CC} + 0.3	2.0	V _{CC} + 0.3	2.0	V _{CC} + 0.3	V
V _{IL}	Input LOW Voltage ^[1]		-0.3	0.8	-0.3	0.8	-0.3	0.8	-0.3	0.8	V
I _{IX}	Input Load Current	GND ≤ V _I ≤ V _{CC}	-1	+1	-1	+1	-1	+1	-1	+1	μA
I _{OZ}	Output Leakage Current	GND ≤ V _I ≤ V _{CC} , Output Disabled	-1	+1	-1	+1	-1	+1	-1	+1	μA
I _{OS} ^[2]	Output Short Circuit Current	V _{CC} = Max., V _{OUT} = GND		-300		-300		-300		-300	mA
I _{CC}	V _{CC} Operating Supply Current	V _{CC} = Max., I _{OUT} = 0 mA, f = f _{MAX} = 1/t _{RC}		85		80		75		70	mA
I _{SB1}	Automatic CE Power-down Current —TTL Inputs	Max. V _{CC} , $\overline{CE} \geq V_{IH}$, V _{IN} ≥ V _{IH} or V _{IN} ≤ V _{IL} , f = f _{MAX}		15		15		15		15	mA
I _{SB2}	Automatic CE Power-down Current —CMOS Inputs	Max. V _{CC} , $\overline{CE} \geq V_{CC} - 0.3V$, V _{IN} ≥ V _{CC} - 0.3V, or V _{IN} ≤ 0.3V, f = 0		5		5		5		5	mA

Capacitance^[3]

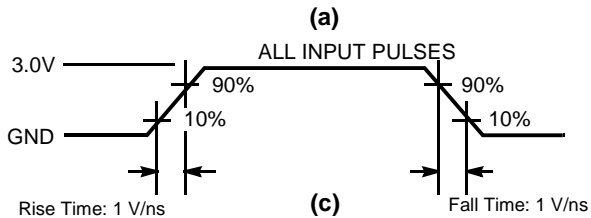
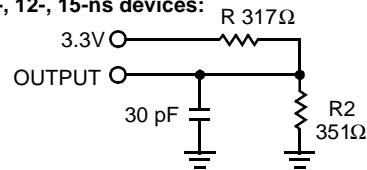
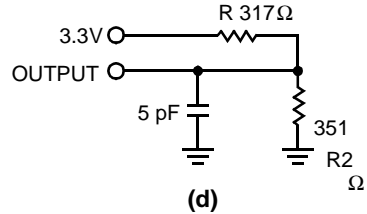
Parameter	Description	Test Conditions	Max.	Unit
C _{IN}	Input Capacitance	T _A = 25°C, f = 1 MHz, V _{CC} = 5.0V	8	pF
C _{OUT}	Output Capacitance		8	pF

Notes:

- V_{IL} (min.) = -2.0V for pulse durations of less than 20 ns.
- Not more than one output should be shorted at one time. Duration of the short circuit should not exceed 30 seconds.
- Tested initially and after any design or process changes that may affect these parameters.

AC Test Loads and Waveforms^[4]
8-ns devices:


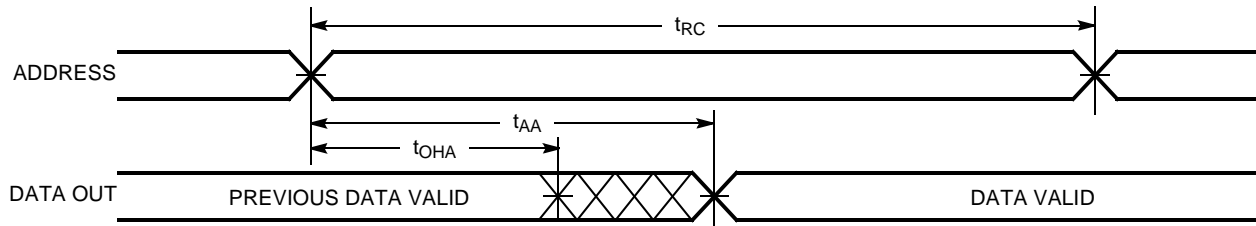
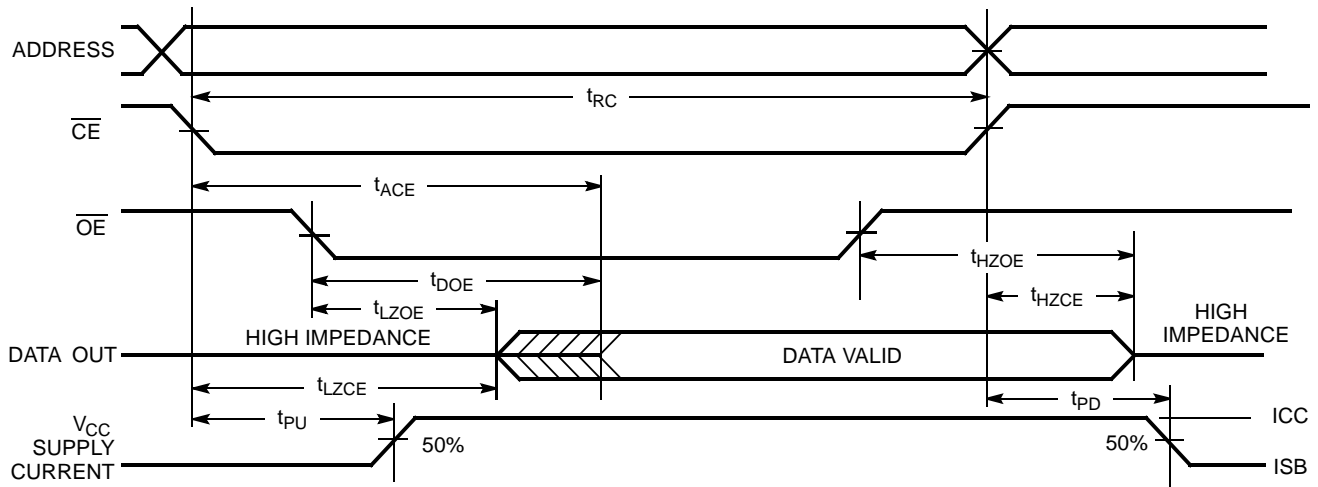
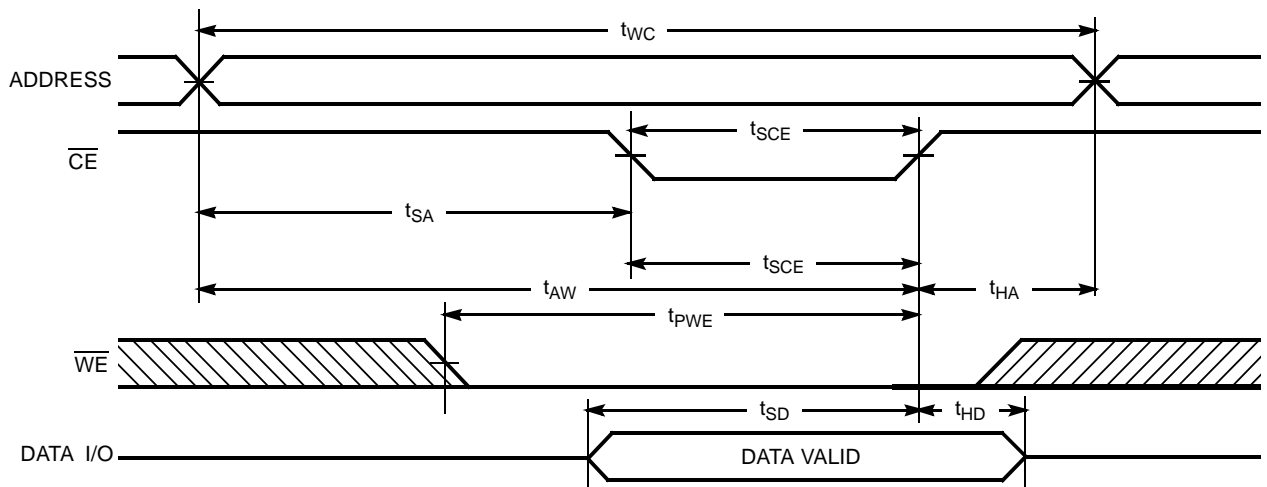
* CAPACITIVE LOAD CONSISTS OF ALL COMPONENTS OF THE TEST ENVIRONMENT

10-, 12-, 15-ns devices:

High-Z characteristics:

Switching Characteristics^[5] Over the Operating Range

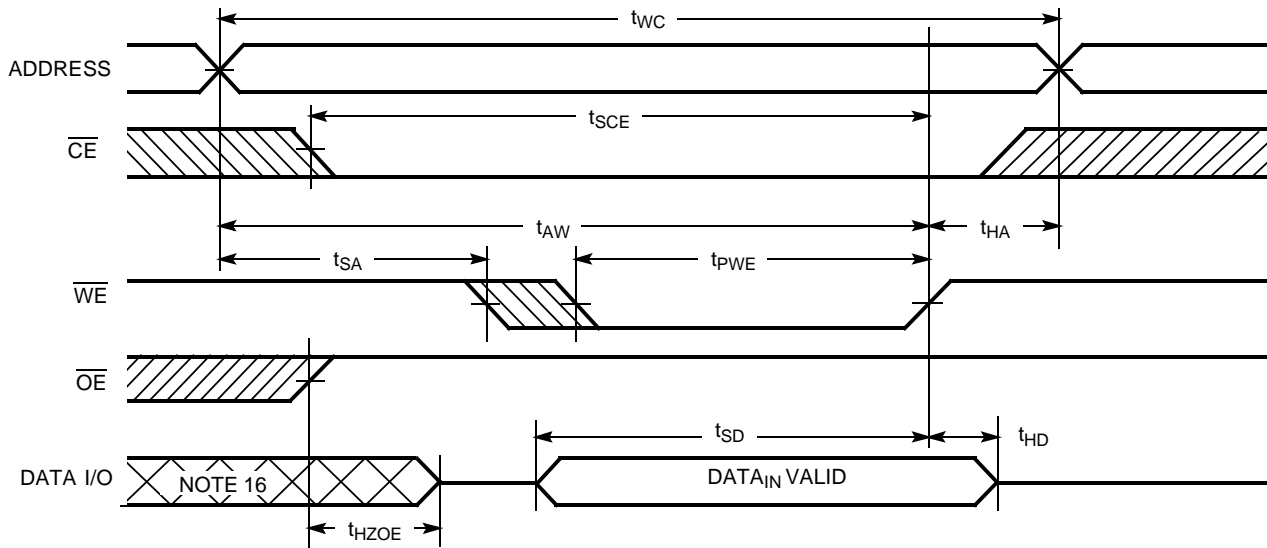
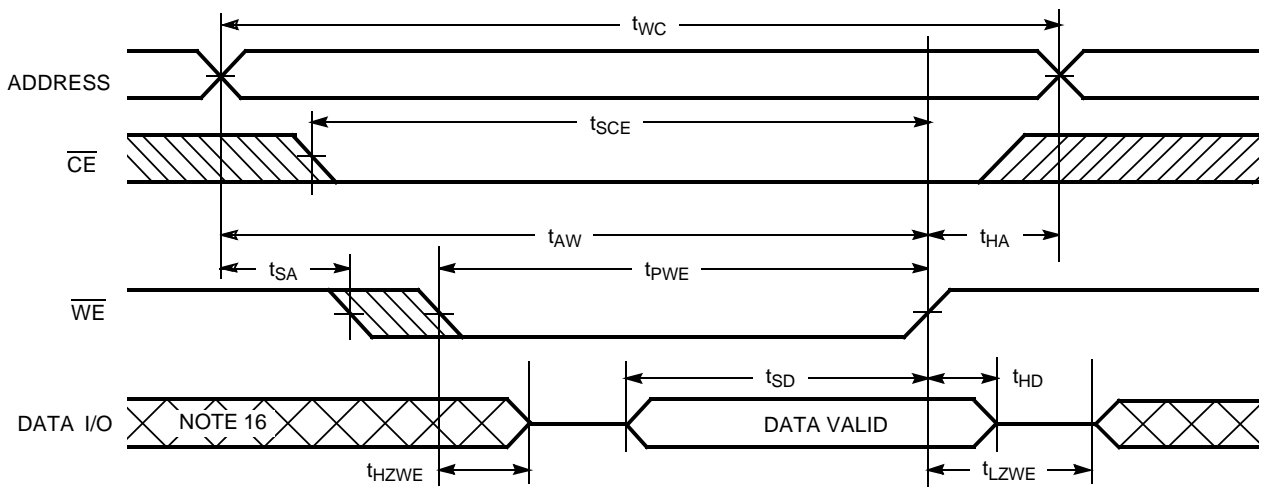
Parameter	Description	7C1019CV33-8		7C1019CV33-10		7C1019CV33-12		7C1019CV33-15		Unit
		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Read Cycle										
t_{RC}	Read Cycle Time	8		10		12		15		ns
t_{AA}	Address to Data Valid		8		10		12		15	ns
t_{OHA}	Data Hold from Address Change	3		3		3		3		ns
t_{ACE}	CE LOW to Data Valid		8		10		12		15	ns
t_{DOE}	OE LOW to Data Valid		5		5		6		7	ns
t_{LZOE}	OE LOW to Low Z	0		0		0		0		ns
t_{HZOE}	OE HIGH to High Z ^[6, 7]		4		5		6		7	ns
t_{LZCE}	CE LOW to Low Z ^[7]	3		3		3		3		ns
t_{HZCE}	CE HIGH to High Z ^[6, 7]		4		5		6		7	ns
t_{PU} ^[8]	CE LOW to Power-Up	0		0		0		0		ns
t_{PD} ^[8]	CE HIGH to Power-Down		8		10		12		15	ns
Write Cycle^[9, 10]										
t_{WC}	Write Cycle Time	8		10		12		15		ns
t_{SCE}	CE LOW to Write End	7		8		9		10		ns
t_{AW}	Address Set-Up to Write End	7		8		9		10		ns
t_{HA}	Address Hold from Write End	0		0		0		0		ns
t_{SA}	Address Set-Up to Write Start	0		0		0		0		ns
t_{PWE}	WE Pulse Width	6		7		8		10		ns
t_{SD}	Data Set-Up to Write End	5		5		6		8		ns
t_{HD}	Data Hold from Write End	0		0		0		0		ns
t_{LZWE}	WE HIGH to Low Z ^[7]	3		3		3		3		ns
t_{HZWE}	WE LOW to High Z ^[6, 7]		4		5		6		7	ns

Notes:

- AC characteristics (except High-Z) for all 8-ns parts are tested using the load conditions shown in Figure (a). All other speeds are tested using the Thevenin load shown in Figure (b). High-Z characteristics are tested for all speeds using the test load shown in Figure (d).
- Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V.
- t_{HZOE} , t_{HZCE} , and t_{HZWE} are specified with a load capacitance of 5 pF as in part (d) of AC Test Loads. Transition is measured ± 500 mV from steady-state voltage.
- At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE} , t_{HZOE} is less than t_{LZOE} , and t_{HZWE} is less than t_{LZWE} for any given device.
- This parameter is guaranteed by design and is not tested.
- The internal write time of the memory is defined by the overlap of \overline{CE} LOW and \overline{WE} LOW. \overline{CE} and \overline{WE} must be LOW to initiate a write, and the transition of any of these signals can terminate the write. The input data set-up and hold timing should be referenced to the leading edge of the signal that terminates the write.
- The minimum write cycle time for Write Cycle no. 3 (WE controlled, OE LOW) is the sum of t_{HZWE} and t_{SD} .

Switching Waveforms
Read Cycle No. 1^[11, 12]

Read Cycle No. 2 (\overline{OE} Controlled)^[12, 13]

Write Cycle No. 1 (\overline{CE} Controlled)^[14, 15]

Notes:

11. Device is continuously selected. $\overline{OE}, \overline{CE} = V_{IL}$.
12. \overline{WE} is HIGH for read cycle.
13. Address valid prior to or coincident with \overline{CE} transition LOW.
14. Data I/O is high impedance if $\overline{OE} = V_{IH}$.
15. If \overline{CE} goes HIGH simultaneously with \overline{WE} going HIGH, the output remains in a high-impedance state.

Switching Waveforms (continued)
Write Cycle No. 2 ($\overline{\text{WE}}$ Controlled, $\overline{\text{OE}}$ HIGH During Write)^[14, 15]

Write Cycle No. 3 ($\overline{\text{WE}}$ Controlled, $\overline{\text{OE}}$ LOW)^[15]

Truth Table

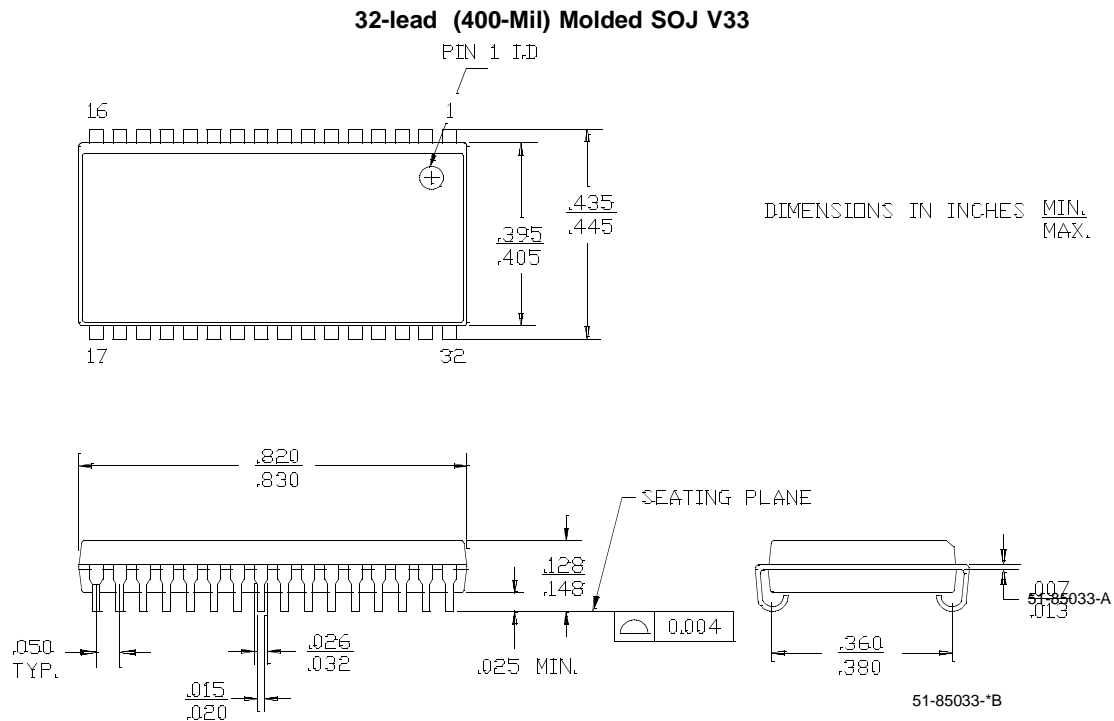
$\overline{\text{CE}}$	$\overline{\text{OE}}$	$\overline{\text{WE}}$	I/O ₀ -I/O ₇	Mode	Power
H	X	X	High Z	Power-Down	Standby (I_{SB})
L	L	H	Data Out	Read	Active (I_{CC})
L	X	L	Data In	Write	Active (I_{CC})
L	H	H	High Z	Selected, Outputs Disabled	Active (I_{CC})

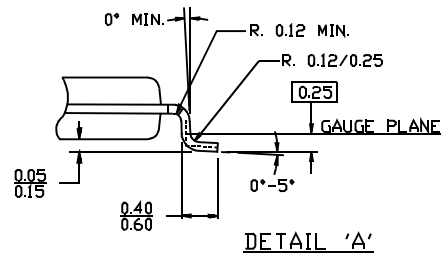
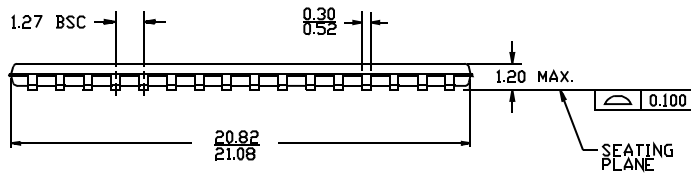
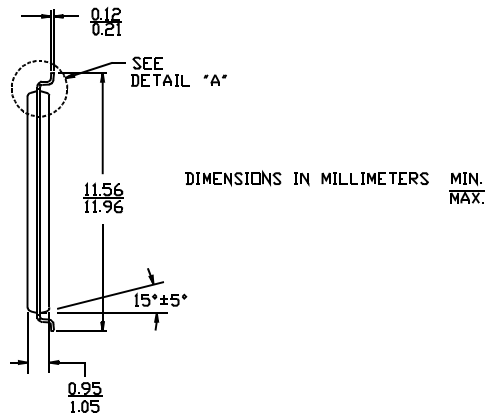
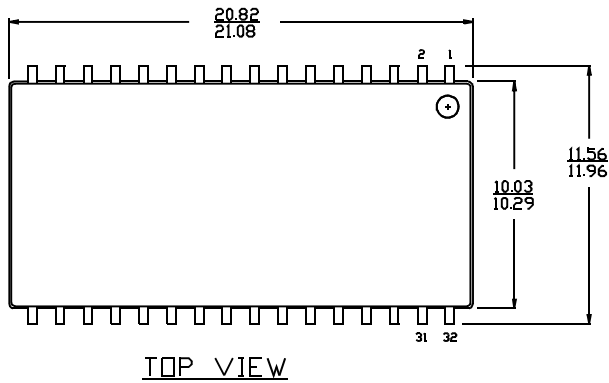
Note:

16. During this period the I/Os are in the output state and input signals should not be applied.

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
8	CY7C1019CV33-8VC	V33	32-Lead 400-Mil Molded SOJ	Commercial
	CY7C1019CV33-8VI	V33	32-Lead 400-Mil Molded SOJ	Industrial
10	CY7C1019CV33-10VC	V33	32-Lead 400-Mil Molded SOJ	Commercial
	CY7C1019CV33-10ZC	ZS32	32-Lead TSOP II	
	CY7C1019CV33-10VI	V33	32-Lead 400-Mil Molded SOJ	Industrial
	CY7C1019CV33-10ZI	ZS32	32-Lead TSOP II	
12	CY7C1019CV33-12VC	V33	32-Lead 400-Mil Molded SOJ	Commercial
	CY7C1019CV33-12ZC	ZS32	32-Lead TSOP II	
	CY7C1019CV33-12VI	V33	32-Lead 400-Mil Molded SOJ	Industrial
	CY7C1019CV33-12ZI	ZS32	32-Lead TSOP II	
15	CY7C1019CV33-15VC	V33	32-Lead 400-Mil Molded SOJ	Commercial
	CY7C1019CV33-15ZC	ZS32	32-Lead TSOP II	
	CY7C1019CV33-15VI	V33	32-Lead 400-Mil Molded SOJ	Industrial
	CY7C1019CV33-15ZI	ZS32	32-Lead TSOP II	

Package Diagram


Package Diagram (continued)
32-lead TSOP II ZS32


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Document History Page

Document Title: CY7C1019CV33 128K x 8 Static RAM Document Number: 38-05130				
REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**	109245	12/16/01	HGK	New Data Sheet
*A	113431	04/10/02	NSL	AC Test Loads split based on speed.
*B	115047	08/01/02	HGK	Added TSOP II Package and I Temp. Improved I _{CC} limits.
*C	119796	10/11/02	DFP	Updated standby current from 5 nA to 5 mA.
*D	123030	12/17/02	DFP	Updated Truth Table to reflect single Chip Enable option.